AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device formed on a substrate, comprising:

an interconnection line formed on said substrate and provided to structure a prescribed circuit; and

a fuse incorporated into said interconnection line,

said fuse and a connection portion of said interconnection line electrically connected to the fuse being formed of different metals, wherein:

the connection portion is selectively blown by a laser beam

~~an oxidation speed of the metal forming said fuse is faster than an oxidation speed of the metal forming the connection portion of said interconnection line;~~

~~said fuse is formed of a copper metal;~~

~~the connection portion of said interconnection line is formed of an aluminum metal; and~~

~~said copper fuse is flat so that focusing can be easily obtained~~.

2. (Cancelled).

3. (Cancelled)

4. (Currently Amended) The semiconductor device according to claim [[1]] 3, wherein

said fuse is formed of the copper metal formed in a damascene process and planarized by a CMP (Chemical Mechanical Polishing) process.

5. (Cancelled).

6. (Original) The semiconductor device according to claim 5, wherein said antireflection layer includes a first antireflection layer extending in a direction of a length of said fuse, and a second antireflection layer extending in a direction traversing the first antireflection layer.

7. (Cancelled).

8. (Original) The semiconductor device according to claim 7, wherein said reflection layer includes a dummy metal line provided between said fuses in a planar view and a transparent resin film covering the dummy metal line, said transparent resin film forming a recessed and protruded surface having a portion overlying the dummy metal line and projecting closer to said fuse than a portion between the dummy metal lines.

9. (Previously Presented) The semiconductor device according to claim 1, wherein said fuse is formed from at least two portions different in width.

10. (Cancelled).

11. (Currently Amended) The semiconductor device according to claim 16 ~~10~~, wherein said fuse has at least three different widths from the end toward the intermediate portion.

12. (New) The semiconductor device according to claim 1, wherein

an oxidation speed of the metal forming said fuse is faster than an oxidation speed of the metal forming the connection portion of said interconnection line.

13. (New) The semiconductor device according to claim 1, wherein

said fuse is formed of a copper metal, and

the connection portion of said interconnection line is formed of an aluminum metal.

14. (New) The semiconductor device according to claim 1, wherein said interconnection line is formed as a multilayer interconnection line,

said fuse is provided at a same layer as one layer of the multilayer interconnection line, and

an antireflection layer is provided closer to said substrate than is a layer of said fuse.

15. (New) The semiconductor device according to claim 1, wherein

said interconnection line is formed as a multilayer interconnection line,

said fuse is provided at a same layer as one layer of the multilayer interconnection line, and

a reflection layer is provided closer to said substrate than is a layer of said fuse.

16. (New) A semiconductor device formed on a substrate, comprising:

an interconnection line formed on said substrate and provided to structure a prescribed circuit; and

a fuse connected to a connection portion of said interconnection line,

said fuse having a width gradually reduced from an end toward an intermediate portion of said fuse, wherein

the connection portion is selectively blown by a laser beam.

17. (New) A method of manufacturing a semiconductor device, the method comprising:

forming a circuit structure with an interconnection line, the interconnection line having a connection portion, on a substrate;

electrically connecting a fuse to the connection portion of the interconnection line, the fuse and the connection portion being formed of different metals; and

selectively blowing the fuse when the circuit structure is to be changed.

18. (New) The method according to claim 17, comprising forming the fuse of a metal having an oxidation speed faster than an oxidation speed of the metal forming the connection portion.

19. (New) The method according to claim 17, comprising:

forming the fuse of a copper metal; and

forming the connection portion of an aluminum metal.

20 (New) The method according to claim 19, comprising forming the copper metal fuse by a damascene process followed by chemical mechanical polishing.

21. (New) The method according to claim 1, comprising:

forming the interconnection line as a multilayer interconnection line;

providing the fuse at a same layer as one layer of the multilayer interconnection line; and

providing an antireflection layer closer to the substrate than is a layer of the fuse.

22. (New) The method according to claim 21, wherein the antireflection layer includes a first antireflection layer extending in the direction of a length of the fuse and a second antireflection layer extending in a direction traversing the first antireflection layer.

23. (New) The method according to claim 1, comprising:

forming the interconnection line as a multilayer interconnection line;

providing the fuse at a same layer as one layer of the multilayer interconnection line; and

providing a reflection layer closer to the substrate than is a layer of the fuse.

24. (New) The method according to claim 22, comprising:

forming a plurality of fuses; and

forming the reflection layer with a dummy metal line provided between the fuses in a planar view and a transparent resin film covering the dummy metal line, the transparent metal film forming a recessed and protruded surface having a portion overlying the dummy metal line and projecting closer to the fuse than a portion between the dummy metal lines.

25. (New) The method according to claim 17, comprising providing a fuse with at least two portions having different widths.